

# Product data sheet

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#### **FEATURES**

For use in low voltage, high frequency inverters Free wheeling, and polarity protection applications.

SOD-123

#### Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25 $^\circ\!\!C$

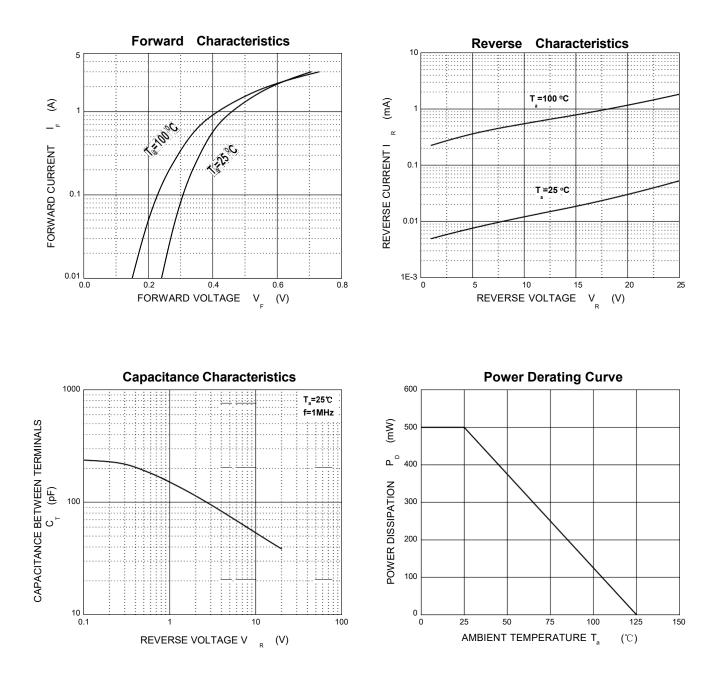
| Parameter   | Symbol   | 1N5819HW-MS | Unit |
|---|--|-------------|------|
| Non-Repetitive Peak Reverse Voltage   | V <sub>RM</sub>  | 40          | V    |
| Peak Repetitive Peak Reverse Voltage<br>Working Peak Reverse Voltage<br>DC Blocking Voltage | V <sub>RRM</sub><br>V <sub>RWM</sub><br>V <sub>R</sub> | 40          | V    |
| RMS Reverse Voltage   | V <sub>R(RMS)</sub>                                    | 28          | V    |
| Average Rectified Output Current  | lo   | 1           | А    |
| Peak Forward Surge Current @t=8.3ms   | I <sub>FSM</sub>                                       | 9           | А    |
| Repetitive Peak Forward Current   | I <sub>FRM</sub>                                       | 1.5         | А    |
| Power Dissipation   | PD   | 500         | mW   |
| Thermal Resistance Junction to<br>Ambient   | R <sub>0JA</sub>                                       | 200         | °C/W |
| Junction temperature  | TJ   | 125         | °C   |
| Storage Temperature   | T <sub>STG</sub>                                       | -55~+150    | °C   |

### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

| Parameter                       | Symbol            | Test conditions                          | Min | Мах        | Unit |
|---------------------------------|-------------------|--|-----|------------|------|
| Reverse breakdown voltage       | V <sub>(BR)</sub> | I <sub>R</sub> = 1mA                     | 40  |            | v    |
| Reverse voltage leakage current | I <sub>R</sub>    | V <sub>R</sub> =40V                      |     | 1          | mA   |
|                                 | V <sub>F</sub>    | I <sub>F</sub> =1A<br>I <sub>F</sub> =3A |     | 0.6<br>0.9 | V    |
| Diode capacitance               | CD                | V <sub>R</sub> =4V, f=1MHz               |     | 120        | pF   |

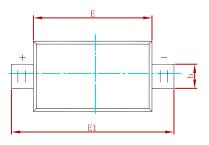


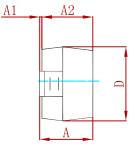
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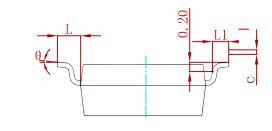




## PACKAGE MECHANICAL DATA

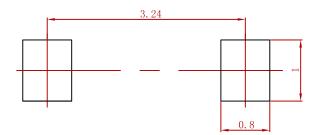






| Symbol | Dimensions | In Millimeters | Dimensions In Inches |       |  |
|--------|------------|----------------|----------------------|-------|--|
| Symbol | Min        | Max            | Min                  | Max   |  |
| A      | 1.050      | 1.250          | 0.041                | 0.049 |  |
| A1     | 0.000      | 0.100          | 0.000                | 0.004 |  |
| A2     | 1.050      | 1.150          | 0.041                | 0.045 |  |
| b      | 0.450      | 0.650          | 0.018                | 0.026 |  |
| С      | 0.080      | 0.150          | 0.003                | 0.006 |  |
| D      | 1.500      | 1.700          | 0.059                | 0.067 |  |
| E      | 2.600      | 2.800          | 0.102                | 0.110 |  |
| E1     | 3.550      | 3.850          | 0.140                | 0.152 |  |
| L      | 0.500 REF  |                | 0.020 REF            |       |  |
| L1     | 0.250      | 0.450          | 0.010                | 0.018 |  |
| θ      | 0°         | 8°             | 0°                   | 8°    |  |

## Suggested Pad Layout



#### Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

| P/N         | PKG     | QTY  |
|-------------|---------|------|
| 1N5819HW-MS | SOD-123 | 3000 |
|             |         |      |



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